Abstracts

Session 8 Introduction (1984 [MWSYM])

S. Temple. "Session 8 Introduction (1984 [MWSYM])." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 213-213.

During the past five years FET device and amplifier circuit technology has advanced significantly. Five years ago, the papers presented at the MTT Symposium in Orlando, Florida reflected the activity within the microwave community to demonstrate the feasibility of 1 watt FET power amplifiers over narrow band-widths in C and X-band. During the next few years, as device process technology was refined to enhance device yields and extend producible power device designs to submicron gate geometries, circuit techniques were being successfully applied to FET power amplifiers providing 1 watt over an octave in X and Ku-band.

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